

FIG. 1A

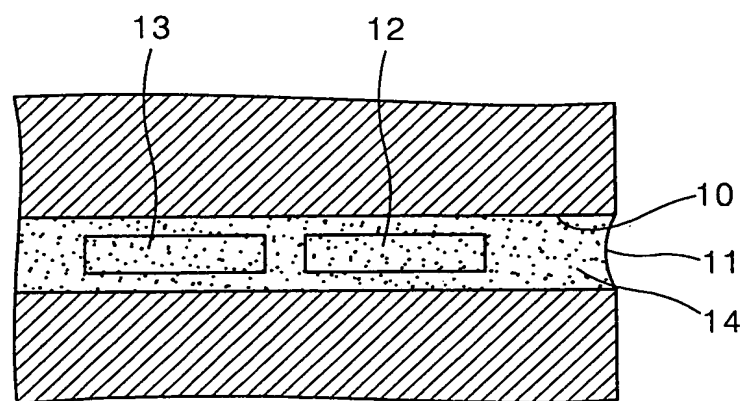


FIG. 1B

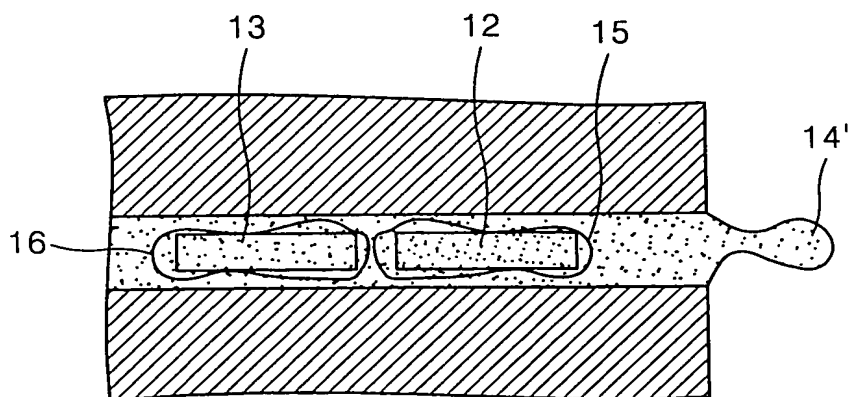


FIG. 2

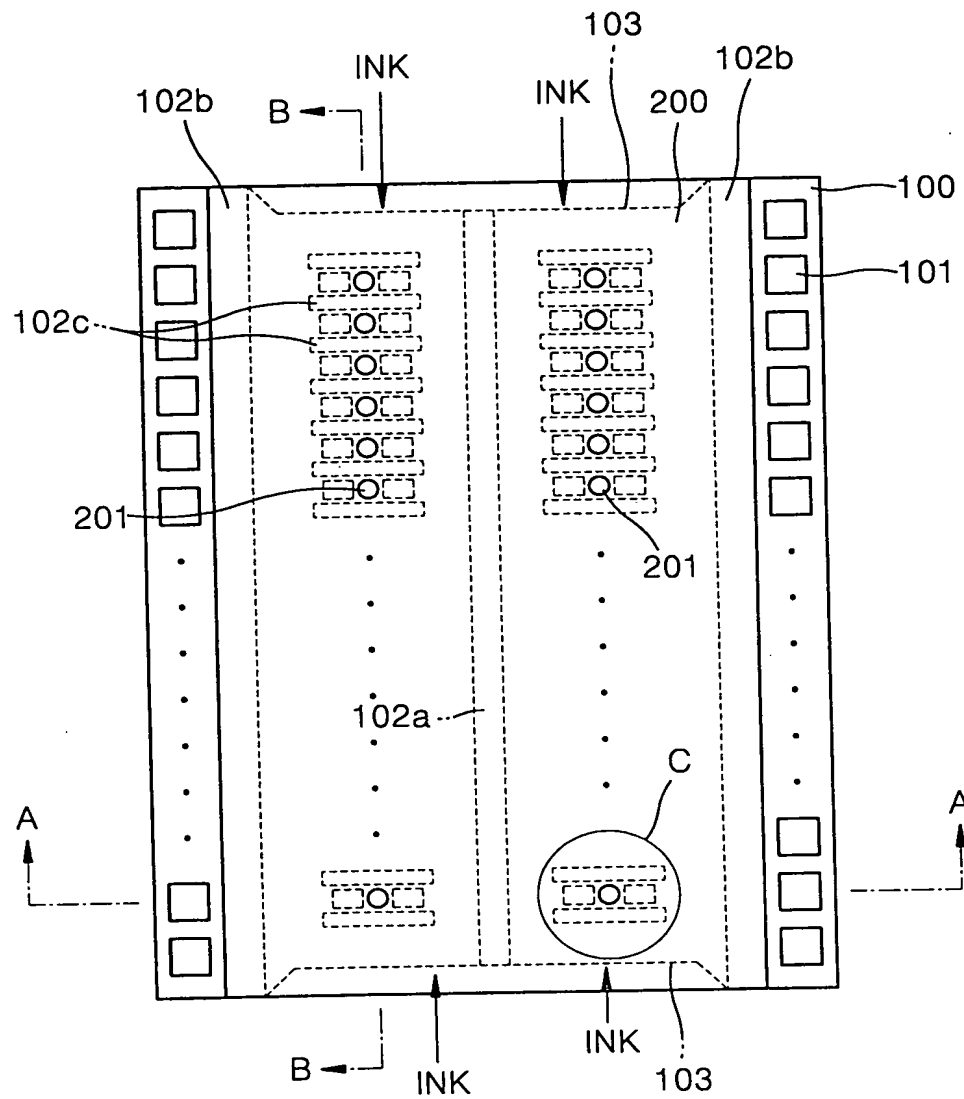


FIG. 3

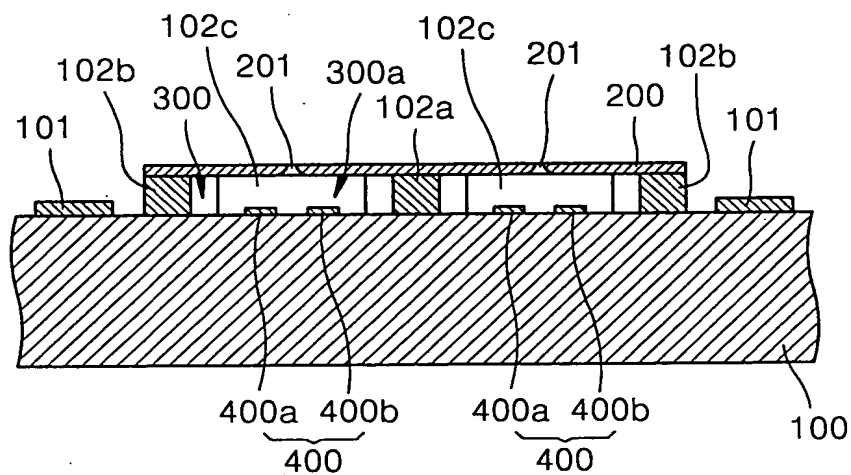


FIG. 4

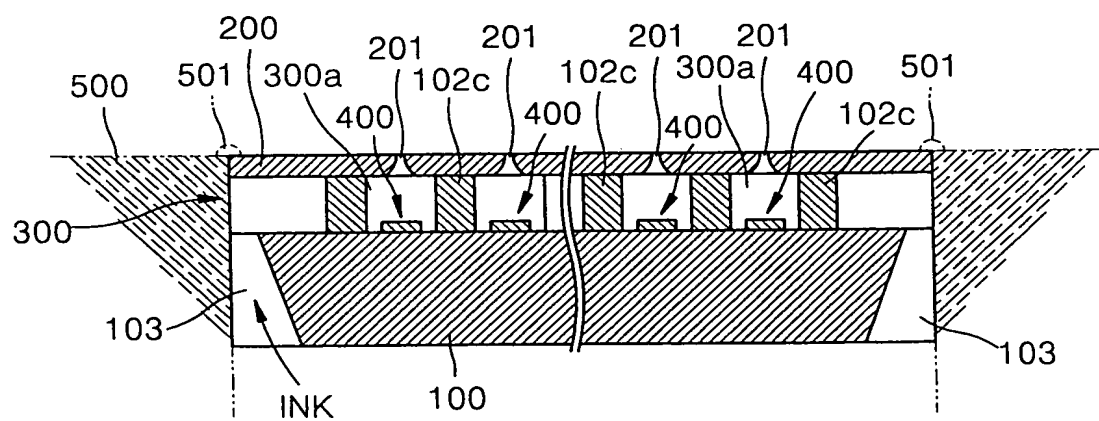


FIG. 5

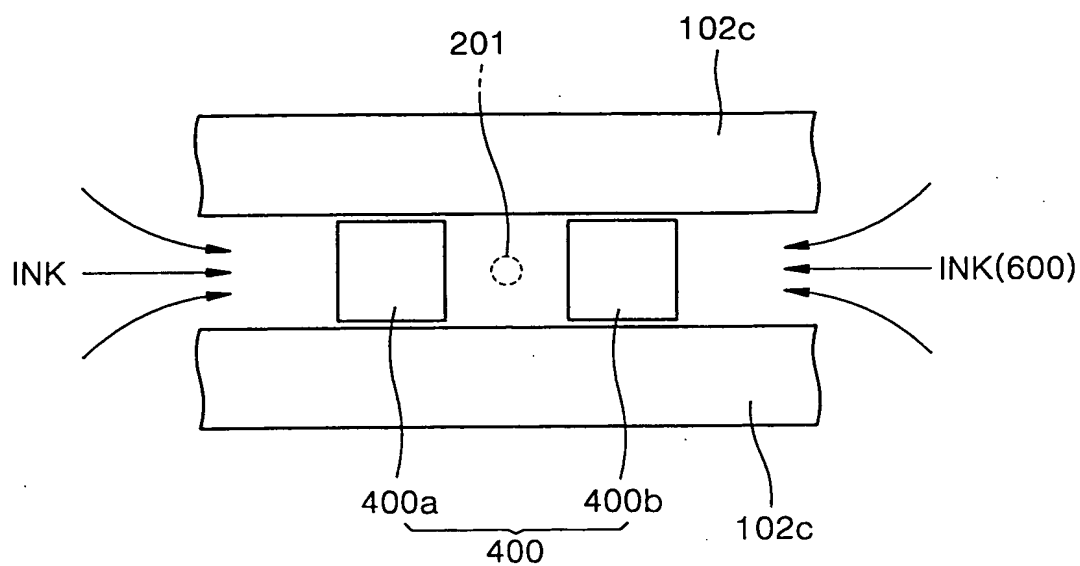


FIG. 6

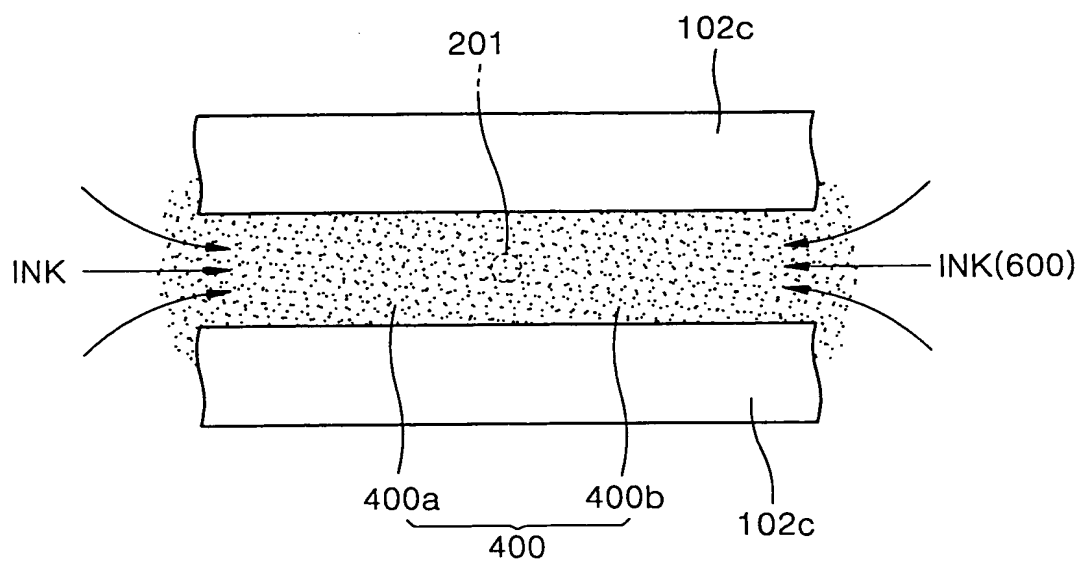


FIG. 7

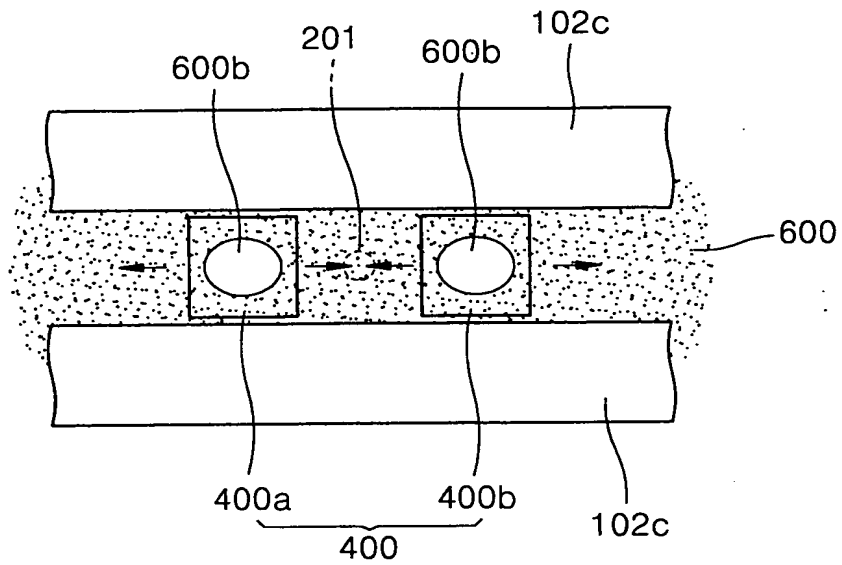


FIG. 8

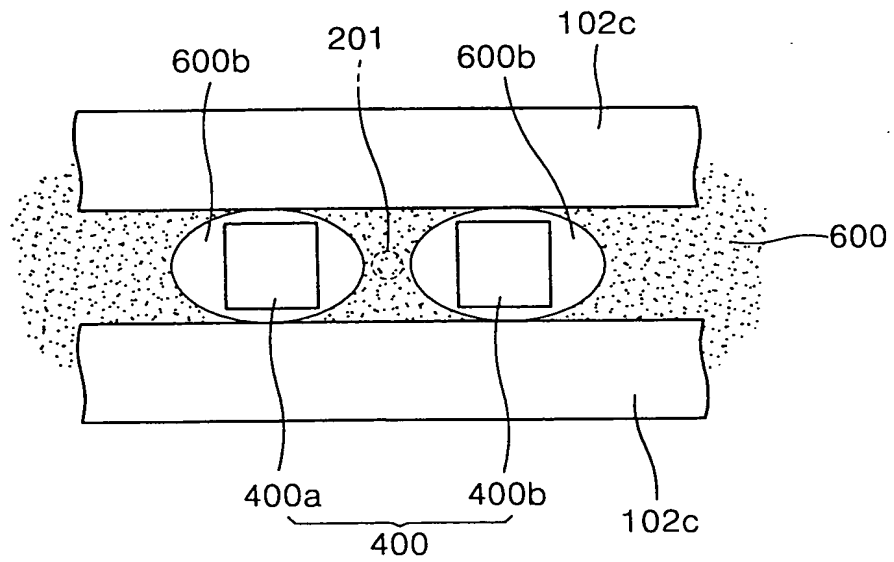


FIG. 9A

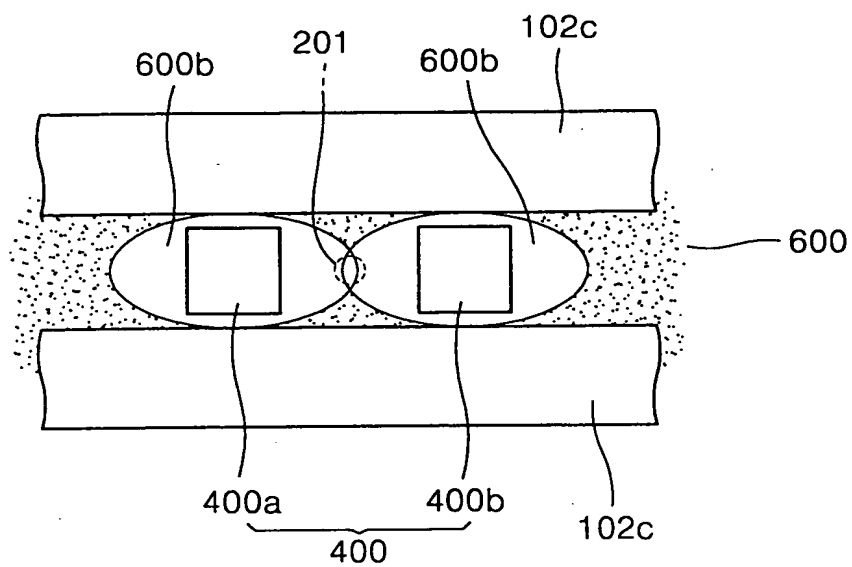
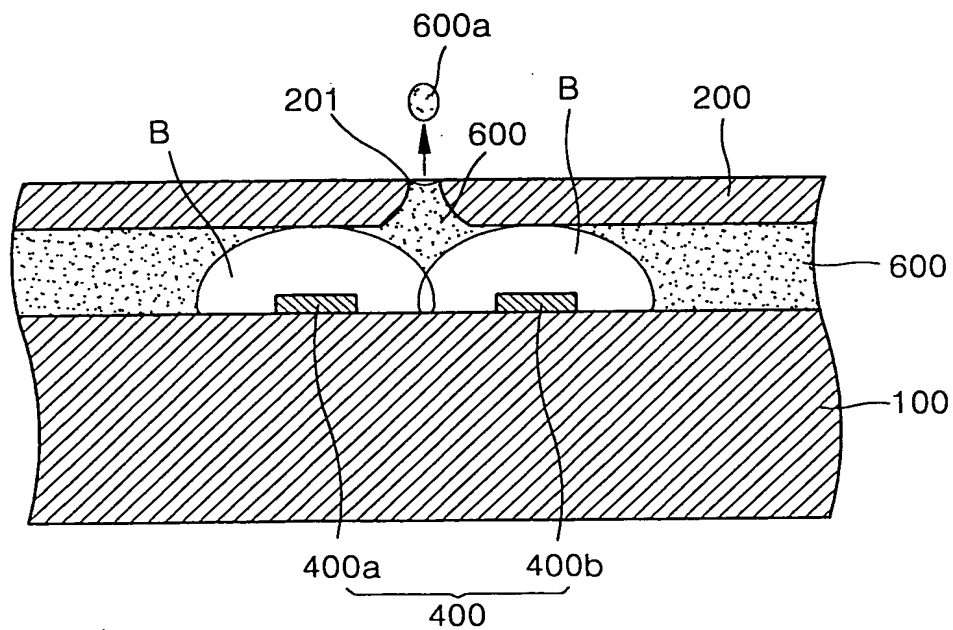


FIG. 9B



[illegible]

A cross-sectional view of a semiconductor device. A substrate 100 is shown with diagonal hatching. On top of the substrate is a first conductive layer 601, also with diagonal hatching. Above the first conductive layer is a second conductive layer 602, shown with a cross-hatched pattern. A patterned conductive layer 101a' is formed on top of the second conductive layer, featuring several rectangular openings. Two specific openings are labeled 400a and 400b, which are grouped together by a bracket labeled 400.



FIG. 13

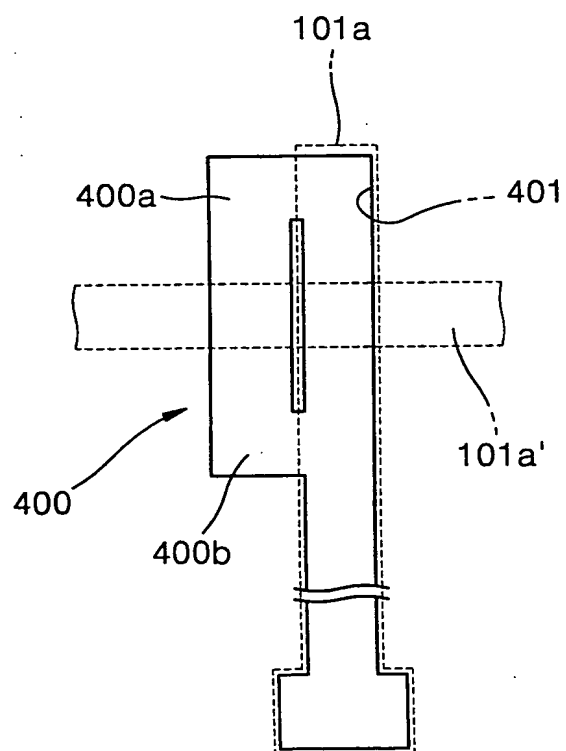


FIG. 14

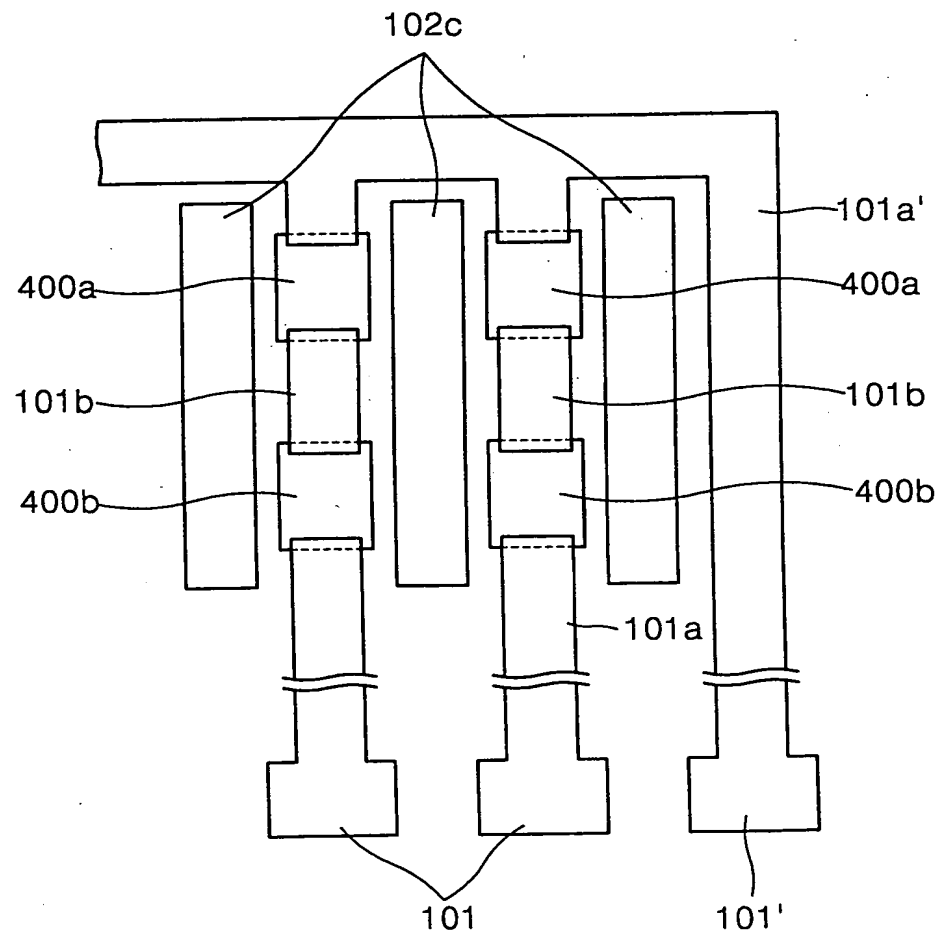


FIG. 15A

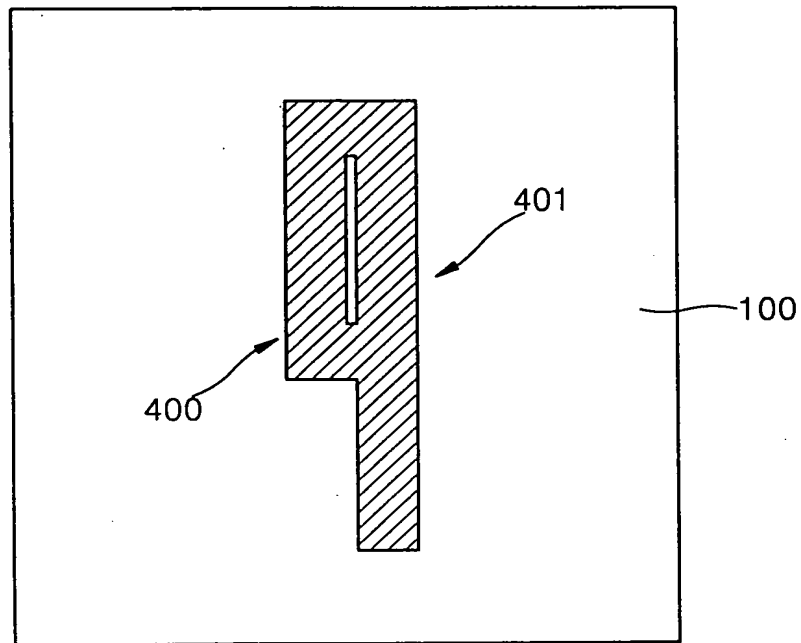


FIG. 15B

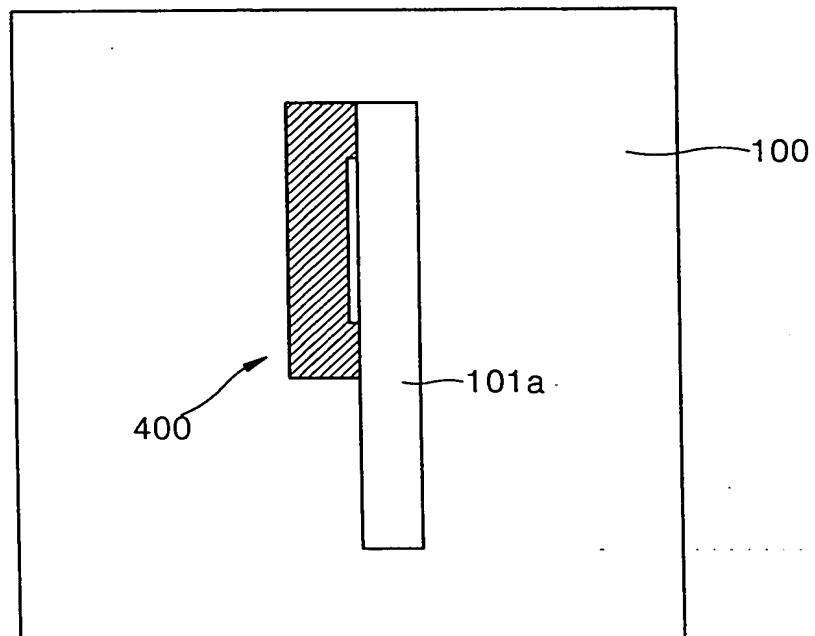


FIG. 15C

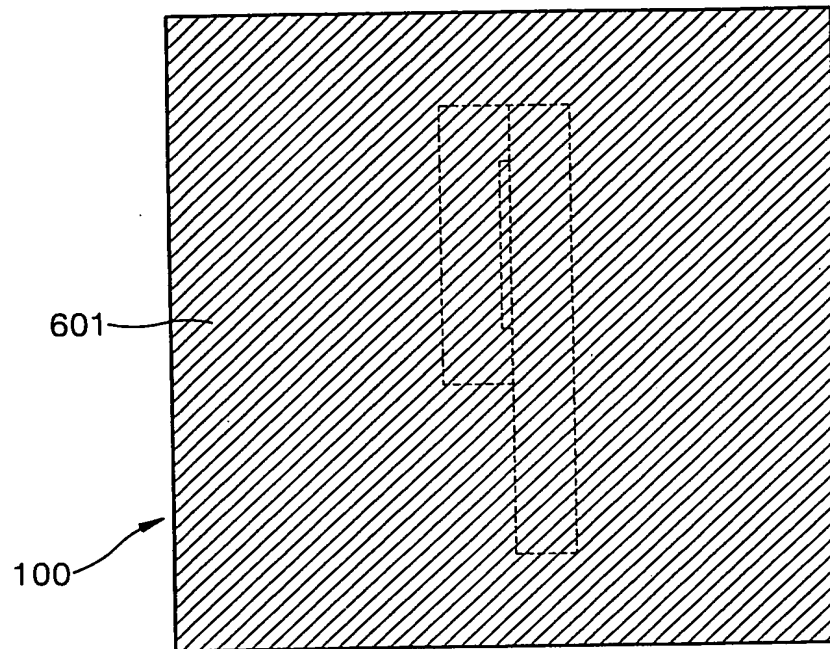


FIG. 15D

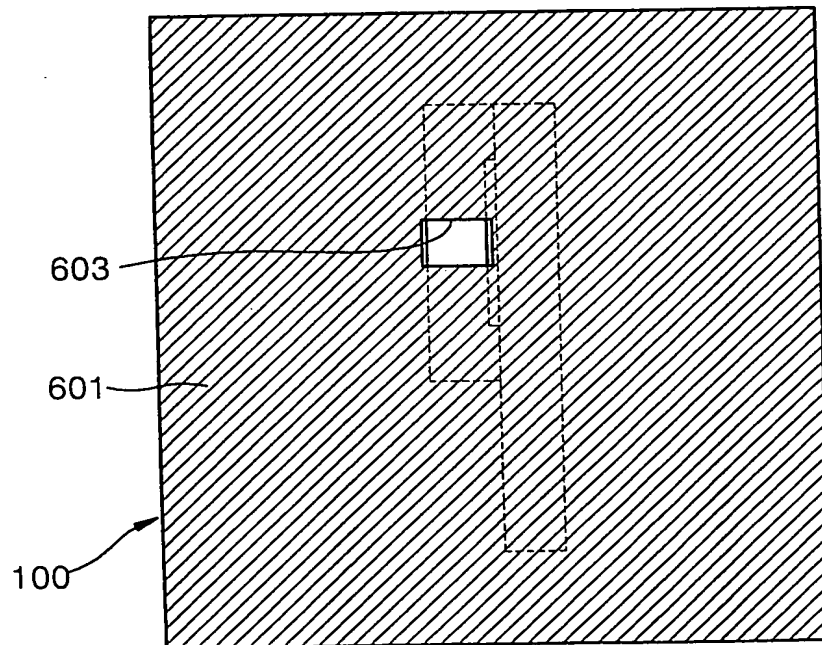


FIG. 15E

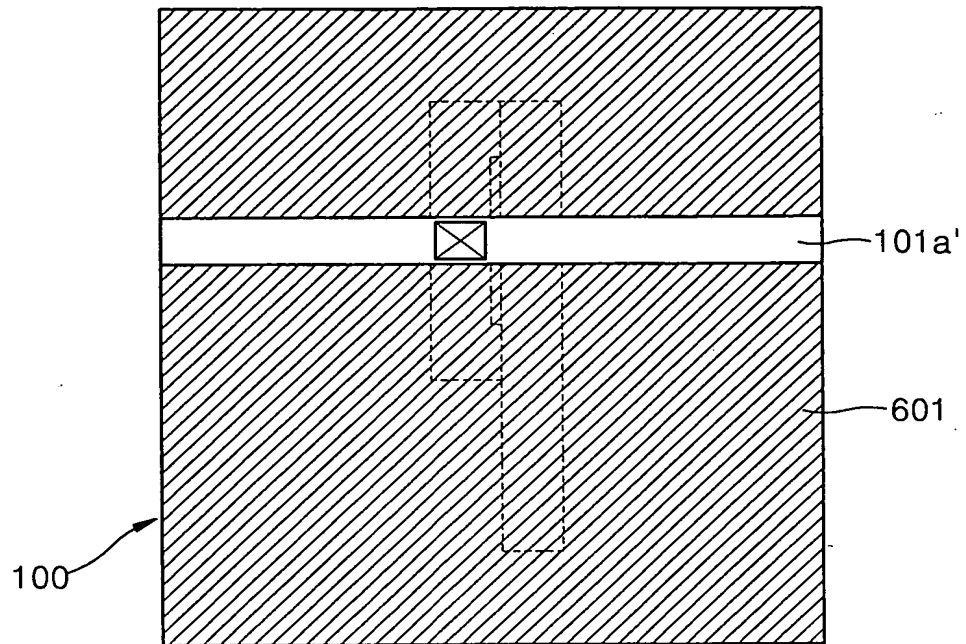


FIG. 15F

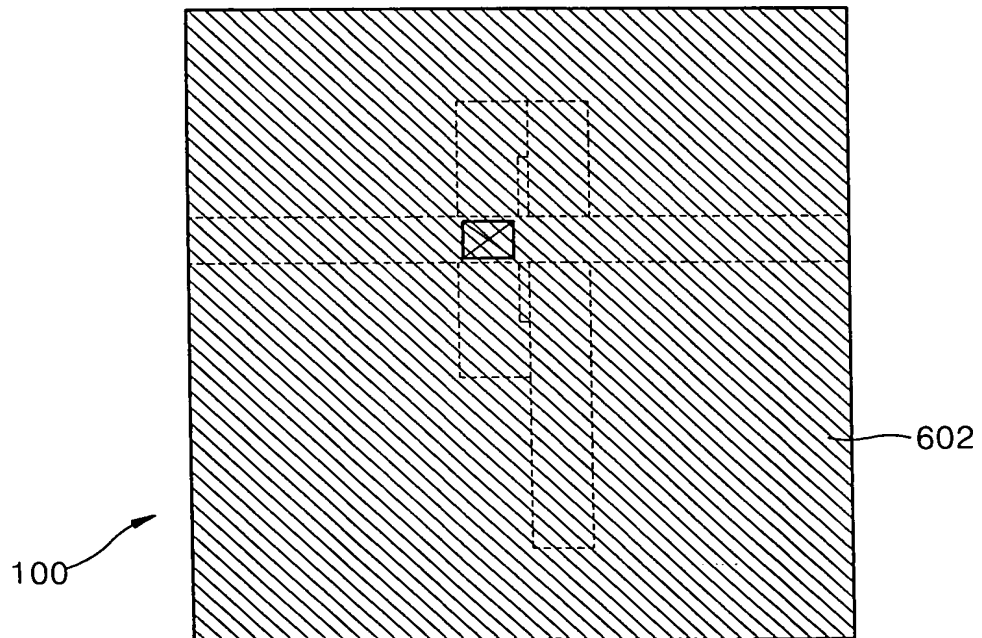


FIG. 15G

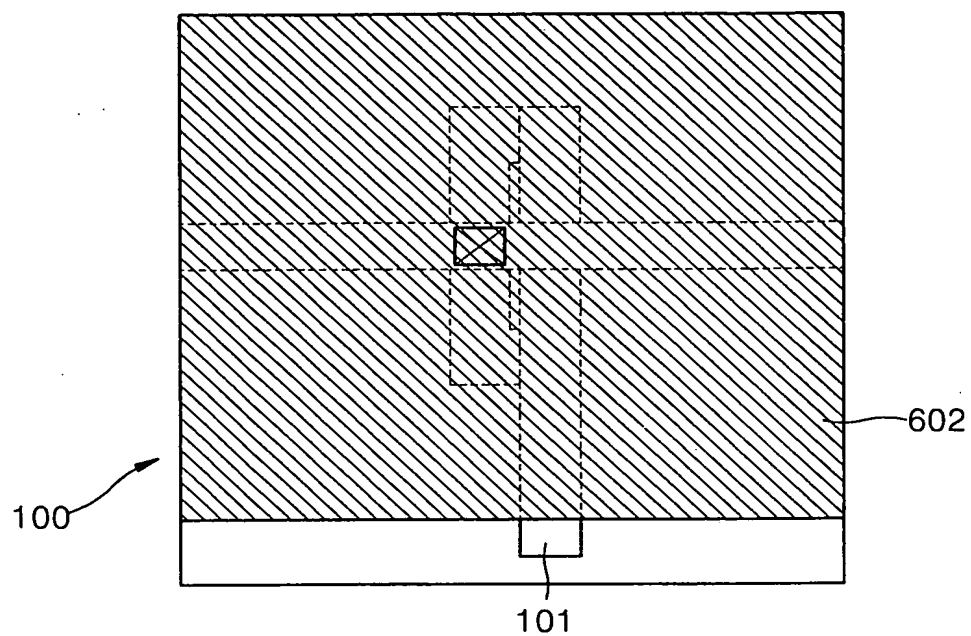


FIG. 15H

